ABSTRACT

SEMICONDUCTOR WAFER AND MANUFACTURING METHOD THEREOF

The present invention provides a semiconductor wafer having sag formed at an outer periphery at the time of polishing, wherein a displacement of the semiconductor wafer in a thickness direction is 100 nm or less between a center and a outer peripheral sag start position of the semiconductor wafer, and the center of the semiconductor wafer has a convex shape, an amount of outer peripheral sag of the semiconductor wafer is 100 nm or less, and the outer peripheral sag start position is away from an outer peripheral portion of the semiconductor wafer toward the center or 20 mm or more away from an outer peripheral end of the semiconductor wafer toward the center, the outer peripheral portion being a measurement target of ESFQR. As a result, an object is to provide a semiconductor wafer that can meet a plurality of flatness indexes, and a manufacturing method thereof.

FIG. 1